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Date of Deposit: June 21, 2005

JC09 Rec'd PCT/PTO 21 JUN 2005

Case No. 9905/30

Client No. BIF023241/US

UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
FOURNEL et al. )  
Serial No.: Not Yet Assigned ) Examiner:  
Filing Date: Herewith ) Not Yet Assigned  
For: METHOD OF PRODUCING )  
MIXED SUBSTRATES AND ) Group Art Unit:  
STRUCTURE THUS OBTAINED ) Not Yet Assigned  
)

X3

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Dear Sir:

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following references:

No.	Date of Publication	Patentee/Applicant/Country
US 2001/0007367 A1	07/12/2001	Ohkubo
6,096,433	08/01/2000	Kikuchi et al.
6,013,954	01/11/2000	Hamajima
5,661,316	08/26/1997	Kish, Jr. et al.
5,138,422	08/11/1992	Fujii et al.
4,920,396	04/24/1990	Shinohara et al.
FR 2 819 099 A1	12/28/2000	France
EP 0 889 509 A2	01/07/1999	EPO
K.Y. Ahn et al., "Growth, Shrinkage, And Stability Of Interfacial Oxide Layers Between Directly Bonded Silicon Wafers," published In Applied Physics A, 50, 1990, pp. 85-94).		
D.M. Garnier et al., "The Fabrication Of A Partial Soi Substrate," Proceedings Of The 9th International Symposium On Silicon On Isolator Technology And Devices, 1999, Vol. 99, Ch. 54, pp. 73-78.		
A. Laporte et al., "Charged Defects At The Interface Between Directly Bonded Silicon Wafers."		
T.Y. Tan et al., "On Oxygen Precipitation Retardation/Recovery Phenomena, Nucleation Incubation Phenomena, And The Exigent-Accommodation-Volume Factor Of Precipitation," Proceedings Of The Fifth International Symposium On Silicon Materials Science And Technology; Semiconductor Silicon 198 Electrochem, Soc, Pennington, Nj, USA; 1986, pp. 864-73).		

K. Terada et al., "A New DRAM Cell With A Transistor On A Lateral Epitaxial Silicon Layer (Tole Cell)," published In IEEE Transactions On Electron Device, Vol. 37, N° 9, Sept. 1990, pp. 2052-7.  
H. Yamaguchi et al, "Intelligent Power IC With Partial Soi Structure," published In Jpn. J. Appl. Phys. Vol. 34 (1995), pp. 864-868.

For the Examiner's convenience, Applicants are enclosing Form PTO-1449 (one sheet). Applicants respectfully request the Examiner's consideration of the above references and entry thereof into the record of this application.

In accordance with 37 C.F.R. §1.98(a)(3), the applicants state that the document FR 2 819 099 A1 discloses a method for producing a stacked structure. A non-certified English translation of the Abstract is enclosed herewith.

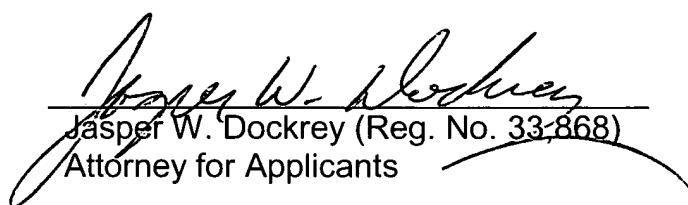
Also enclosed is a copy of the International Search Report issued on May 28, 2004 for corresponding PCT Application No. PCT/FR03/03867 of the above-identified application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

June 21, 2005

  
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Jasper W. Dockrey (Reg. No. 33,868)  
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Attorney for Applicants

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FORM PTO-1449	SERIAL NO. Not Yet Assigned	CASE NO. 9905/30 (BIF023241/US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE Herewith	GROUP ART UNIT Not Yet Assigned
APPLICANTS: FOURNEL et al.		

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	A1	US 2001/0007367 A1	07/12/2001	Ohkubo		
	A2	6,096,433	08/01/2000	Kikuchi et al.		
	A3	6,013,954	01/11/2000	Hamajima		
	A4	5,661,316	08/26/1997	Kish, Jr. et al.		
	A5	5,138,422	08/11/1992	Fujii et al.		
	A6	4,920,396	04/24/1990	Shinohara et al.		

## FOREIGN PATENT DOCUMENT

FOREIGN PARENT DOCUMENT						
EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	A7	FR 2 819 099 A1	12/28/2000	France		no
	A8	EP 0 889 509 A2	01/07/1999	EPO		

**EXAMINER  
INITIAL**

## OTHER ART – NON PATENT LITERATURE DOCUMENTS

(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)

	A9	K.Y. Ahn et al., "Growth, Shrinkage, And Stability Of Interfacial Oxide Layers Between Directly Bonded Silicon Wafers," published In Applied Physics A, 50, 1990, pp. 85-94).
	A10	D.M. Garnier et al., "The Fabrication Of A Partial Soi Substrate," Proceedings Of The 9th International Symposium On Silicon On Isolator Technology And Devices, 1999, Vol. 99, Ch. 54, pp. 73-78.
	A11	A. Laporte et al., "Charged Defects At The Interface Between Directly Bonded Silicon Wafers."
	A12	T.Y. Tan et al., "On Oxygen Precipitation Retardation/Recovery Phenomena, Nucleation Incubation Phenomena, And The Exigent-Accommodation-Volume Factor Of Precipitation," Proceedings Of The Fifth International Symposium On Silicon Materials Science And Technology; Semiconductor Silicon 198 Electrochem, Soc, Pennington, Nj, USA; 1986, pp. 864-73).
	A13	K. Terada et al., "A New Dram Cell With A Transistor On A Lateral Epitaxial Silicon Layer (Tole Cell)," published In IEEE Transactions On Electron Device, Vol. 37, N° 9, Sept. 1990, pp. 2052-7.
	A14	H. Yamaguchi et al, "Intelligent Power IC With Partial Soi Structure," published In Jpn, J. Appl. Phys. Vol. 34 (1995), pp. 864-868.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.